

Taiwan Goodark Technology Co.,Ltd

CESD5V0D3

ESD Protection Diodes

DESCRIPTION

The CESD5V0D3 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.



FEATURES

- Stand-off Voltage:3.3V-12 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limits	Unit				
IEC61000-4-2(ESD)		±15	ΚV				
	Contact		±8.0	NV.			
ESD voltage po		30	KV				
Total power dissipation on FR-5 board (N	P _D	200	mW				
Thermal Resistance Junction-to-Ambie	R⊝JA	625	°C/W				
Lead Solder Temperature - Maximum (TL	260	°C				
Junction and Storage temperature range	T _j , T _{stg}	-55 ~ +150	°C				

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended. Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

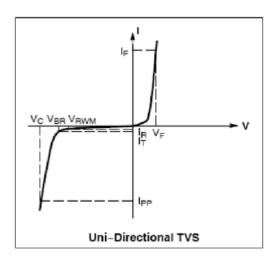


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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Clamping Voltage @ I _{PP} Working Peak Reverse Voltage Maximum Reverse Leakage Current @ V _{RWM} Breakdown Voltage @ I _T Test Current	Symbol
Working Peak Reverse Voltage Maximum Reverse Leakage Current @ V _{RWM} Breakdown Voltage @ I _T Test Current	I PP
Maximum Reverse Leakage Current @ V _{RWM} Breakdown Voltage @ I _T Test Current	Vc
Breakdown Voltage @ I _T Test Current	V _{RWM}
Test Current	I _R
	V_{BR}
Face would Commont	I _T
Forward Current	I _F
Forward Voltage @ I _F	V _F
Peak Power Dissipation	Ppk
Max. Capacitance @V _R =0 and f =1MHz	С



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, $V_F = 0.9 \lor Max$. @ $I_F = 10mA$ for all types)

Device*	Device	V _{RWM}	I _R (μΑ) @ V _{RWM}	V _{BR} @ I _T (N		I _T	Vc @IPP = 5 A	Ipp(A)	V₂(V) @Max I _{PP} †	P _{pk} + (W)	C (pF)
	Marking	Max	Max	Min	Max	mA	V	Max	Max	Max	Тур
CESD3V3D3	YU	3.3	10	5.0	5.9	1.0	9.3	15	13.5	350	450
CESD5V0D3	ZA	5.0	10	6.2	7.3	1.0	9.8	15	15.5	350	350
CESD12VD3	ZC	12	1.0	13.3	15.75	1.0	22	12	33	350	150

^{*}Other voltages available upon request.

⁺Surge current waveform per Figure 6.

^{2.} V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.